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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/890,143	07/26/2001	Masaki Yamamoto	SHIG19990241	7584
21171 STAAS & HAL	7590 02/13/200 SEY LLP	EXAMINER		
SUITE 700		KAO, CHIH CHENG G		
1201 NEW YORK AVENUE, N.W. WASHINGTON, DC 20005			ART UNIT	PAPER NUMBER
			2882	
			MAIL DATE	DELIVERY MODE
			02/13/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Applica	tion No.	Applicant(s)			
Office Action Summary		09/890,	143	YAMAMOTO, MASAKI			
		Examin		Art Unit			
		Chih-Ch	eng Glen Kao	2882			
	MAILING DATE of this commu			the correspondence address			
Period for Re	· -		TO EVOIDE AMON	UTLICO FROM			
THE MAIL - Extensions of after SIX (6) - If the period - If NO period - Failure to re Any reply re	ENED STATUTORY PERIOD F ING DATE OF THIS COMMUN of time may be available under the provision MONTHS from the mailing date of this com for reply specified above is less than thirty (for reply is specified above, the maximum s ply within the set or extended period for repl ceived by the Office later than three months nt term adjustment. See 37 CFR 1.704(b).	NICATION. us of 37 CFR 1.136(a). In no of the immunication. (30) days, a reply within the statutory period will apply and by will, by statute, cause the a	event, however, may a reply atutory minimum of thirty (3 will expire SIX (6) MONTH pplication to become ABAN	y be timely filed 60) days will be considered timely. S from the mailing date of this communication. DONED (35 U.S.C. § 133).			
Status							
1)⊠ Resp	consive to communication(s) fil	led on 22 January 20	008.				
•	This action is FINAL . 2b) This action is non-final.						
3)☐ Sinc							
close	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition o	f Claims						
4)⊠ Clair	m(s) <u>31-59</u> is/are pending in the	e application.					
4a) C	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)⊠ Clair	Claim(s) <u>37</u> is/are allowed.						
6)⊠ Clair	Claim(s) <u>31-36 and 38-59</u> is/are rejected.						
7)∐ Clair	Claim(s) is/are objected to.						
8)⊡ Clair	Claim(s) are subject to restriction and/or election requirement.						
Application P	apers						
9)∏ The s	specification is objected to by the	he Examiner.					
10)⊠ The o	0)⊠ The drawing(s) filed on <u>02 September 2003</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.						
Appli	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Repla	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) <u></u> The o	oath or declaration is objected t	to by the Examiner. I	Note the attached C	Office Action or form PTO-152.			
Priority under	[•] 35 U.S.C. § 119						
12)⊠ Ackn a)⊠ All 1.⊠	<i>,</i> — <i>,</i> —		_	19(a)-(d) or (f).			
2.□	Certified copies of the priority			lication No			
3.	•	•					
	application from the Internation	onal Bureau (PCT R	ule 17.2(a)).				
* See th	ne attached detailed Office action	on for a list of the ce	rtified copies not red	ceived.			
Attachment(s)	- ((DTO 440)			
	eferences Cited (PTO-892) raftsperson's Patent Drawing Review (PTO-948)		nmary (PTO-413) ⁄Iail Date			
3) Information	Disclosure Statement(s) (PTO-1449 o)/Mail Date			rmal Patent Application (PTO-152)			

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 22, 2008, has been entered.

Claim Objections

2. Claims 38-59 are objected to because of the following informalities, which appear to be minor draft errors including grammatical and/or lack of antecedent problems.

In the following format (location of objection; suggestion for correction), the following correction(s) may obviate the objection(s): (claim 38, last line; inserting --that-- before "would have been"), (claim 48, last line; replacing "would be" with --that would have been--), (claim 49, last line; replacing "would be" with --that would have been--), and (claim 59, line 8, "said portion is cut away"; replacing "portion is" with --portions are--).

Claims 39-47 and 50-58 are objected to by virtue of their dependency. For purposes of examination, the claims have been treated as such. Appropriate correction is required.

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Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the

basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on

sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 31, 32, 38, 39, 42-44, 46, 48-50, 53-55, and 57 are rejected under 35

U.S.C. 102(b) as being anticipated by Itou et al. (US 5272744).

4. Regarding claims 31, 49, and 50, Itou et al. discloses a method comprising forming on a

substrate (fig. 6d, #1) a multilayer film stack (fig. 6d, #2) of alternating layers of high refractive

index material and low refractive index material (col. 5, lines 16-20), and cutting away a portion

of the multilayer film stack (fig. 6c, #2) so that at least one layer successively arranged from an

outermost surface of the multilayer film stack has a predetermined portion in which material of

the respective layer does not exist (fig. 6c, #2) so that the respective layer is thereby non-uniform

across the multilayer film stack (fig. 6d, #2), wherein the multilayer film stack, having said

portion cut away, reflects radiation in a range from vacuum ultraviolet through X-ray (col. 1,

lines 5-7), more than one alternating layer of high refractive index material and low refractive

index material of the multilayer film stack (fig. 6d, #2), having said portion cut away, necessarily

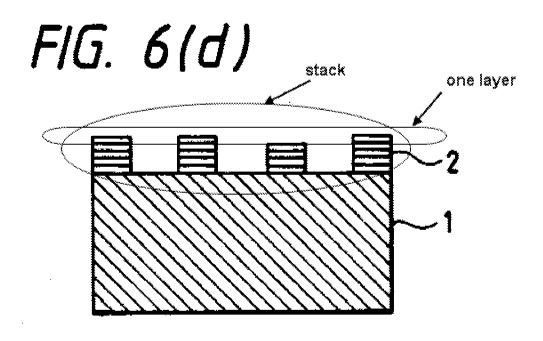
adjusts a wavefront phase of emerging rays, and said cutting away cuts away said portion to

thereby change the wavefront phase where said portion is cut away in accordance with an

amount of adjustment of the wavefront phase, wherein the wavefront phase where said portion

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does not exist (fig. 6d) is necessarily different than the wavefront phase that would have if said portion existed (fig. 6a; and col. 5, lines 37-46).



- 5. Regarding claims 32, 42, 53, and 54 Itou et al. further discloses wherein the multilayer film stack is formed in a number of cycles larger than that necessary to saturate a reflectance (col. 5, lines 41-43).
- 6. Regarding claim 38, Itou et al. discloses a multilayer film reflection mirror that reflects radiation in a range from vacuum ultraviolet through X-ray (col. 1, lines 5-7) comprising: a multilayer film (fig. 6d, #2) formed by a plurality of repeated pairs of layers, layers of each pair of layers having different refractive indexes from each other (col. 5, lines 16-20), at least one layer successively arranged from an outermost surface of the multilayer film having a

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predetermined portion in which material of the respective layer does not exist (via cutting in fig.

6c) so that the respective layer is thereby non-uniform across the multilayer film (fig. 6d, #2),

and more than one pair of layers among said plurality of repeated pairs of layers necessarily

adjusting a wavefront phase of a light reflected by said multilayer film (fig. 6d, #2), wherein the

wavefront phase where said portion does not exist (fig. 6d) is necessarily different than the

wavefront phase that would have been if said portion had existed (fig. 6a).

7. Regarding claim 39, Itou et al. further discloses wherein said wavefront phase is adjusted

with more than one layer among said plurality of repeated pairs being partially removed (col. 5,

lines 26-29).

8. Regarding claim 43, Itou et al. further discloses wherein said wavefront phase is adjusted

with more than one layer among the pairs of layers where the reflectivity is already saturated

(col. 5, lines 41-43) being partially removed (fig. 6d, #2).

9. Regarding claims 44 and 55, Itou et al. further discloses wherein reflectivity of said

multilayer film is between about 15% and about 80% (col. 5, lines 41-43).

10. Regarding claims 46 and 57, Itou et al. further discloses wherein said multilayer film is

formed by pairs of molybdenum and silicon layers (col. 5, lines 16-20).

11. Regarding claim 48, Itou et al. further discloses an exposure apparatus (col. 1, lines 5-7). Application/Control Number: 09/890,143 Page 6

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Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are

such that the subject matter as a whole would have been obvious at the time the invention was made to a person

having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the

manner in which the invention was made.

12. Claim 33 is rejected under 35 U.S.C. 103(a) as being unpatentable over Itou et al. as

applied to claim 31 above, and further in view of Sweeney et al. (US 6235434).

Itou et al. as recited above discloses a method as recited above.

However, Itou et al. fails to disclose wherein the cutting away is controlled by detecting a

difference in a material.

Sweeney et al. teaches wherein cutting away is controlled by detecting a difference in a

material (col. 4, lines 57-60).

It would have been obvious, to one having ordinary skill in the art at the time the

invention was made, to modify the method of Itou et al. with the detecting and control of

Sweeney et al., since one would have been motivated to make such a modification for ensuring

appropriate correction (col. 4, lines 57-60) as shown by Sweeney et al.

Furthermore, since the Examiner finds that the prior art contained a "base" method upon

which the claimed invention can be seen as an "improvement", and since the Examiner finds that

the prior art contained a comparable method that was improved in the same way as the claimed

invention, the Examiner finds that one of ordinary skill in the art could have applied the known

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"improvement" technique in the same way to the "base" method and the results would have been

predictable to one of ordinary skill in the art. Therefore, such a claimed combination is obvious.

13. Claim 34 is rejected under 35 U.S.C. 103(a) as being unpatentable over Itou et al. and

Sweeney et al. as applied to claim 33 above, and further in view of Smith (US 4590376).

Itou et al. as modified above suggests a method as recited above.

However, Itou et al. fails to disclose wherein a difference in material is detected by

monitoring a secondary electron discharge.

Smith teaches wherein a difference in material is detected by monitoring a secondary

electron discharge (col. 1, lines 6-12).

It would have been obvious to one having ordinary skill in the art at the time the

invention was made, to further modify the method of Itou et al. as modified above with the

monitoring of Smith, since one would have been motivated to make such a modification for

better monitoring quality (col. 1, line 12) as implied from Smith.

14. Claims 35 and 36 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itou et

al. and Sweeney et al. as applied to claim 33 above, and further in view of Iketaki (US 5163078).

Itou et al. as modified above suggests a method as recited above.

However, Itou et al. fails to disclose wherein a difference in material is detected by

monitoring an optical change of characteristics, wherein said optical change of characteristics

monitored is a change in an optical constant of visible rays or a change based on ellipsometry.

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Iketaki teaches wherein a difference in material is detected by monitoring an optical change of characteristics, wherein said optical change of characteristics monitored is a change in an optical constant of visible rays or a change based on ellipsometry (col. 5, lines 25-31).

It would have been obvious to one having ordinary skill in the art at the time the invention was made, to further modify the method of Itou et al. as modified above with the monitoring of Iketaki, since one would have been motivated to make such a modification for better keeping film fabrication within tolerances (col. 5, lines 25-31) as shown by Iketaki.

15. Claims 40, 41, 51, and 52 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itou et al. as applied to claims 39 and 50 above, and further in view of Montcalm et al. (US 6110607).

Itou et al. as recited above discloses a device and method as recited above. Itou et al. further discloses wherein removal of a multilayer film is stopped at a portion of a layer (col. 5, lines 29-31), which creates an outermost layer.

However, Itou et al. fails to disclose an outermost layer having a relatively higher refractive index among layers with different refractive indexes from each other, wherein said layer having a relatively higher refractive index is made of silicon.

Montcalm et al. teaches an outermost layer having a relatively higher refractive index among layers with different refractive indexes from each other, wherein said layer having a relatively higher refractive index is made of silicon (col. 4, lines 25-28).

It would have been obvious, to one having ordinary skill in the art at the time the invention was made, to modify the device and method of Itou et al. with the outermost layer of Montcalm et al., since one would have been motivated to make such a modification for

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increasing reflectivity (col. 4, lines 25-28) as shown by Montcalm et al.

16. Claims 45, 47, 56, and 58 are rejected under 35 U.S.C. 103(a) as being unpatentable over

Itou et al. as applied to claims 38 and 49 above, and further in view of Ceglio et al. (US

5691541).

17. Regarding claims 45 and 56, Itou et al. discloses a device and method as recited above.

However, Itou et al. fails to disclose wherein said light is an EUV light.

Ceglio et al. teaches wherein light is an EUV light (col. 4, lines 5-20).

It would have been obvious, to one having ordinary skill in the art at the time the

invention was made, to modify the device and method of Itou et al. with the EUV light of Ceglio

et al., because of the following rationale.

Since the Examiner finds that the prior art contained a "base" device and method upon

which the claimed invention can be seen as an "improvement", and since the Examiner finds that

the prior art contained a comparable device and method that was improved in the same way as

the claimed invention, the Examiner finds that one of ordinary skill in the art could have applied

the known "improvement" technique in the same way to the "base" device and method and the

results would have been predictable to one of ordinary skill in the art. Therefore, such a claimed

combination is obvious.

18. Regarding claims 47 and 58, Itou et al. discloses a device and method as recited above. However, Itou et al. fails to disclose wherein said multilayer film is one of a multilayer film formed by pairs of ruthenium and silicon layers, a multilayer film formed by pairs of rhodium and silicon layers, a multilayer film formed by pairs of ruthenium and carbon layers, or a multilayer film formed by pairs of rhodium and carbon layers.

Ceglio et al. teaches wherein said multilayer film is one of a multilayer film formed by pairs of ruthenium and silicon layers (col. 4, lines 5-20), multilayer film formed by pairs of rhodium and silicon layers, a multilayer film formed by pairs of ruthenium and carbon layers, or a multilayer film formed by pairs of rhodium and carbon layers.

It would have been obvious, to one having ordinary skill in the art at the time the invention was made, to modify the device and method of Itou et al. as recited above with the layers of Ceglio et al., because of the following rationale.

Since the Examiner finds that the prior art contained a device and method which differed from the claimed device and method by the substitution of some element with another element, and since the Examiner finds that the substituted elements and their functions were known in the art, the Examiner thus finds that one of ordinary skill in the art could have substituted one known element for another, and the results of the substitution would have been predictable. Therefore, such a claimed combination is obvious.

19. Claim 59 is rejected under 35 U.S.C. 103(a) as being unpatentable over Sweeney et al. in view of Yamamoto et al. (Layer-by-layer design method for soft-x-ray multilayers).

Sweeney et al. discloses an optical element comprising a substrate (fig. 1, #120) having a multilayer film (fig. 1, #110) formed thereon, the multilayer film having a stack of alternating

layers of high refractive index material and low refractive index material in a number of cycles (col. 3, lines 38-40); and a correction film (fig. 1, #130) on the multilayer film (fig. 1, #110), wherein the optical element reflects radiation in a range from vacuum ultraviolet through X-ray (col. 3, lines 32-43).

However, Sweeney et al. fails to disclose wherein a multilayer film stack is formed in a number of cycles larger than that necessary to substantially saturate a reflectance.

Yamamoto et al. teaches wherein a multilayer film stack is formed in a number of cycles larger than that necessary to substantially saturate a reflectance (fig. 9).

It would have been obvious to one having ordinary skill in the art at the time the invention was made, to modify the device of Sweeney et al. with the number of cycles of Yamamoto et al., since one would have been motivated to make such a modification for ensuring that enough reflectance is obtained (fig. 9; and pg. 1629, col. 2, second full paragraph) as implied from Yamamoto et al., which will maximize the radiation intensity and the efficiency of the system.

Furthermore, since the Examiner finds that the prior art (i.e., Sweeney et al.) contained a "base" device upon which the claimed invention can be seen as an "improvement", and since the Examiner finds that the prior art (i.e., Yamamoto et al.) contained a comparable device that was improved in the same way as the claimed invention, the Examiner thus finds that one of ordinary skill in the art could have applied the known "improvement" technique in the same way to the "base" device and the results would have been predictable to one of ordinary skill in the art. Therefore, such a claimed combination is obvious.

from the prior art.

Also note that claim scope is not limited by claim language (i.e., "wherein ... the correction film and the stack each have a cut away portion to thereby change a wavefront phase of emerging rays where said portions are cut away corresponding to an amount of adjustment of the wavefront phase) that does not limit a claim to a particular structure. In other words, there is no distinctive structural characteristic claimed that differentiates the optical element as claimed

Allowable Subject Matter

20. Claim 37 is allowed. The following is a statement of reasons for the indication of allowable subject matter.

Regarding claim 37, the prior art fails to disclose or fairly suggest a method for forming an optical element that reflects radiation in a range from vacuum ultraviolet through X-ray, including the step of cutting away a portion of a correction film and a multilayer film stack in accordance with an amount of adjustment of a wavefront phase of emerging rays, in combination with all the limitations in the claim.

Response to Arguments

21. Applicant's arguments with respect to claim 59 have been considered but are moot in view of the new ground(s) of rejection. Applicant's arguments filed January 22, 2008, have been fully considered but they are not persuasive.

22. Regarding claims 31, 38, and 49, Applicant argues that the films are not removed to adjust an amount of wavefront phase. The Examiner disagrees. As seen in column 5, lines 37-40, Itou et al. discusses the influence of wavefront phase in relation to defects and projection images. In order to ensure that projection images are not influenced by defects due to their effects on wavefront phases, the films are removed (i.e., the multilayer is repaired to remove the defect) in order to keep the effects of wavefront phase the same as a multilayer free of defects (col. 5, lines 37-40, of Itou et al.). Therefore, film (i.e, a defect) is removed to adjust an amount of wavefront phase.

Applicant further argues that column 5, lines 32-40, of Itou et al. supports Applicant's position, since Applicant believes that the above reading describes the wavefront phase staying the same (i.e., not changing). The Examiner disagrees with this assessment. Itou et al. discloses that the thickness of the removed portion of the multilayer corresponds substantially to an interger multiple of $\lambda/2$ x cos α , so that the phase is not changed (relative to a multilayer free of defect, not a multilayer with a defect). In other words, a hypothetical multilayer free of defect (which is not shown in figs. 6a-6d) has the same phase effects as a defect-repaired multilayer (fig. 6d; and col. 5, lines 43-46). The multilayer with a defect (fig. 6a) does not have the same phase effects as a defect-repaired multilayer (fig. 6d), since the characeteristics of the defect in a multilayer relative to phase effects will necessarily cause a difference compared to the hypothetical multilayer that is defect free (i.e., fig. 6a but without a defect #6).

In conclusion, Applicant's arguments are not persuasive, and the claims remain rejected.

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Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Chih-Cheng Glen Kao whose telephone number is (571) 272-

2492. The examiner can normally be reached on M - F (9 am to 5 pm).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Ed Glick can be reached on (571) 272-2490. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

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like assistance from a USPTO Customer Service Representative or access to the automated

information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Chih-Cheng Glen Kao/ Primary Examiner, Art Unit 2882